

Silicon NPN Power Transistors 2N5622 2N5624 2N5626 2N5628

DESCRIPTION

- With TO-3 package
- Excellent safe operating area
- Low collector saturation voltage

APPLICATIONS

- For audio and general-purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

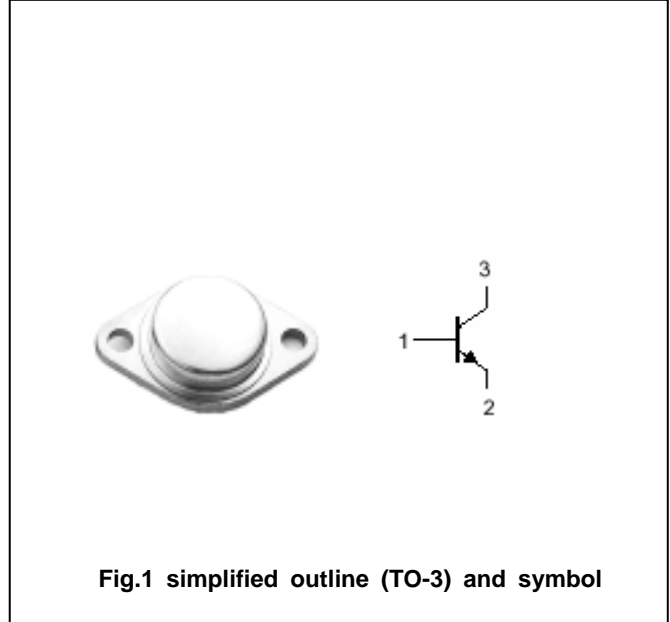


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N5622	80	V
		2N5624/5626	100	
		2N5628	120	
V _{CEO}	Collector-emitter voltage	2N5622	60	V
		2N5624/5626	80	
		2N5628	100	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		10	A
P _D	Total power dissipation	T _C =25	100	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.5	/W

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CHARACTERISTICST_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N5622	I _C =50mA ; I _B =0	60			V
		2N5624/5626		80			
		2N5628		100			
V _{CEsat}	Collector-emitter saturation voltage		I _C =10A; I _B =1A			1.5	V
V _{BE}	Base-emitter on voltage		I _C =5A ; V _{CE} =5V			1.5	V
I _{CBO}	Collector cut-off current		V _{CB} =Rated V _{CB0} ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current		V _{EB} =5V; I _C =0			0.1	mA
h _{FE}	DC current gain	2N5622/5626	I _C =5A ; V _{CE} =5V	70		200	
		2N5624/5628		30		90	
f _T	Transition frequency	2N5622/5626	I _C =1A ; V _{CE} =12V	40			MHz
		2N5624/5628		30			

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PACKAGE OUTLINE

